

SMARTDISCRETES™

Internally Clamped, Current Limited N-Channel Logic Level Power MOSFET

These SMARTDISCRETES devices feature current limiting for short circuit protection, an integral gate-to-source clamp for ESD protection and gate-to-drain clamp for over-voltage protection. No additional gate series resistance is required when interfacing to the output of a MCU, but a 40 kΩ gate pulldown resistor is recommended to avoid a floating gate condition.

The internal gate-to-source and gate-to-drain clamps allow the devices to be applied without use of external transient suppression components. The gate-to-source clamp protects the MOSFET input from electrostatic gate voltage stresses up to 2.0 kV. The gate-to-drain clamp protects the MOSFET drain from drain avalanche stresses that occur with inductive loads. This unique design provides voltage clamping that is essentially independent of operating temperature.

The MLP1N06CL is fabricated using Motorola's SMARTDISCRETES technology which combines the advantages of a power MOSFET output device with on-chip protective circuitry. This approach offers an economical means for providing additional functions that protect a power MOSFET in harsh automotive and industrial environments. SMARTDISCRETES devices are specified over a wide temperature range from -50°C to 150°C.

- Temperature Compensated Gate-to-Drain Clamp Limits Voltage Stress Applied to the Device and Protects the Load From Overvoltage
- Integrated ESD Diode Protection
- Controlled Switching Minimizes RFI
- Low Threshold Voltage Enables Interfacing Power Loads to Microprocessors

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	Clamped	Vdc
Drain-to-Gate Voltage (R _{GS} = 1.0 MΩ)	V _{DGR}	Clamped	Vdc
Gate-to-Source Voltage — Continuous	V _{GS}	±10	Vdc
Drain Current — Continuous — Single Pulse	I _D I _{DM}	Self-limited 1.8	Adc
Total Power Dissipation	P _D	40	Watts
Electrostatic Discharge Voltage (Human Body Model)	ESD	2.0	kV
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-50 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction to Case	R _{θJC}	3.12	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case	T _L	260	°C

UNCLAMPED DRAIN-TO-SOURCE AVALANCHE CHARACTERISTICS

Single Pulse Drain-to-Source Avalanche Energy (Starting T _J = 25°C, I _D = 2.0 A, L = 40 mH) (Figure 6)	E _{AS}	80	mJ
---	-----------------	----	----

SMARTDISCRETES is a trademark of Motorola, Inc.

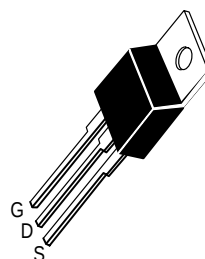
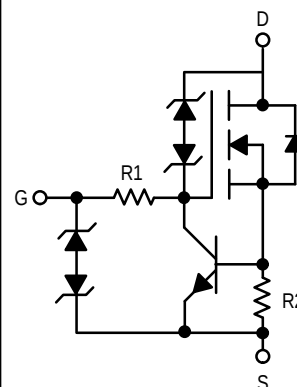
Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1

MLP1N06CL

Motorola Preferred Device

**VOLTAGE CLAMPED
CURRENT LIMITING
MOSFET**
62 VOLTS (CLAMPED)
R_{DS(on)} = 0.75 OHMS



CASE 221A-06, Style 5
TO-220AB



MOTOROLA

MLP1N06CL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-to-Source Sustaining Voltage (Internally Clamped) (I _D = 20 mA, V _{GS} = 0) (I _D = 20 mA, V _{GS} = 0, T _J = 150°C)	V _(BR) DSS	59 59	62 62	65 65	V _{dc}
Zero Gate Voltage Drain Current (V _{DS} = 45 V, V _{GS} = 0) (V _{DS} = 45 V, V _{GS} = 0, T _J = 150°C)	I _{DSS}	— —	0.6 6.0	5.0 20	μA _{dc}
Gate-Body Leakage Current (V _G = 5.0 V, V _{DS} = 0) (V _G = 5.0 V, V _{DS} = 0, T _J = 150°C)	I _{GSS}	— —	0.5 1.0	5.0 20	μA _{dc}

ON CHARACTERISTICS*

Gate Threshold Voltage (I _D = 250 μA, V _{DS} = V _{GS}) (I _D = 250 μA, V _{DS} = V _{GS} , T _J = 150°C)	V _{GS(th)}	1.0 0.6	1.5 —	2.0 1.6	V _{dc}
Static Drain-to-Source On-Resistance (I _D = 1.0 A, V _{GS} = 4.0 V) (I _D = 1.0 A, V _{GS} = 5.0 V) (I _D = 1.0 A, V _{GS} = 4.0 V, T _J = 150°C) (I _D = 1.0 A, V _{GS} = 5.0 V, T _J = 150°C)	R _{DS(on)}	— — — —	0.63 0.59 1.1 1.0	0.75 0.75 1.9 1.8	Ohms
Forward Transconductance (I _D = 1.0 A, V _{DS} = 10 V)	g _{FS}	1.0	1.4	—	mhos
Static Source-to-Drain Diode Voltage (I _S = 1.0 A, V _{GS} = 0)	V _{SD}	—	1.1	1.5	V _{dc}
Static Drain Current Limit (V _{GS} = 5.0 V, V _{DS} = 10 V) (V _{GS} = 5.0 V, V _{DS} = 10 V, T _J = 150°C)	I _{D(lim)}	2.0 1.1	2.3 1.3	2.75 1.8	A

RESISTIVE SWITCHING CHARACTERISTICS*

Turn-On Delay Time	(V _{DD} = 25 V, I _D = 1.0 A, V _{GS} = 5.0 V, R _G = 50 Ohms)	t _{d(on)}	—	1.2	2.0	μs
Rise Time		t _r	—	4.0	6.0	
Turn-Off Delay Time		t _{d(off)}	—	4.0	6.0	
Fall Time		t _f	—	3.0	5.0	

* Indicates Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

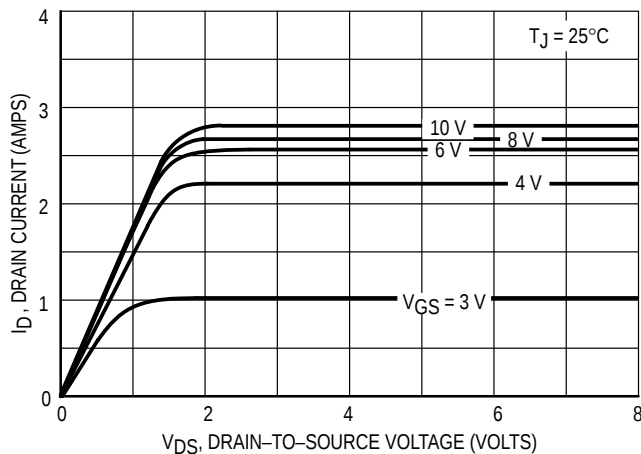


Figure 1. Output Characteristics

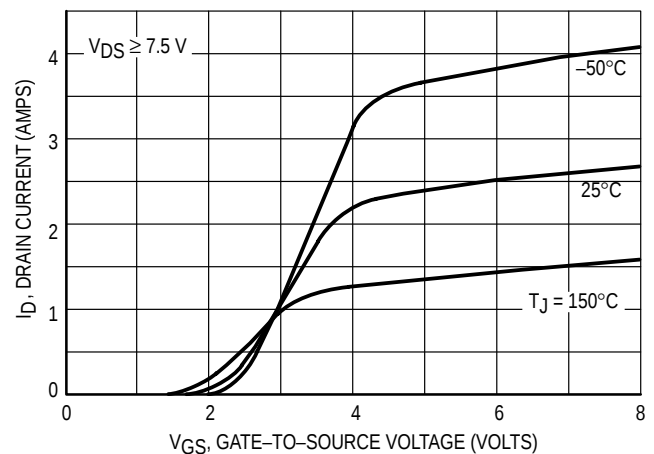


Figure 2. Transfer Function

THE SMARTDISCRETES CONCEPT

From a standard power MOSFET process, several active and passive elements can be obtained that provide on-chip protection to the basic power device. Such elements require only a small increase in silicon area and/or the addition of one masking layer to the process. The resulting device exhibits significant improvements in ruggedness and reliability as well as system cost reduction. The SMARTDISCRETES device functions can now provide an economical alternative to smart power ICs for power applications requiring low on-resistance, high voltage and high current.

These devices are designed for applications that require a rugged power switching device with short circuit protection that can be directly interfaced to a microcontroller unit (MCU). Ideal applications include automotive fuel injector driver, incandescent lamp driver or other applications where a high in-rush current or a shorted load condition could occur.

OPERATION IN THE CURRENT LIMIT MODE

The amount of time that an unprotected device can withstand the current stress resulting from a shorted load before its maximum junction temperature is exceeded is dependent upon a number of factors that include the amount of heatsinking that is provided, the size or rating of the device, its initial junction temperature, and the supply voltage. Without some form of current limiting, a shorted load can raise a device's junction temperature beyond the maximum rated operating temperature in only a few milliseconds.

Even with no heatsink, the MLP1N06CL can withstand a shorted load powered by an automotive battery (10 to 14 Volts) for almost a second if its initial operating temperature is under 100°C. For longer periods of operation in the current-limited mode, device heatsinking can extend operation from several seconds to indefinitely depending on the amount of heatsinking provided.

SHORT CIRCUIT PROTECTION AND THE EFFECT OF TEMPERATURE

The on-chip circuitry of the MLP1N06CL offers an integrated means of protecting the MOSFET component from high in-rush current or a shorted load. As shown in the schematic diagram, the current limiting feature is provided by an NPN transistor and integral resistors R1 and R2. R2 senses the current through the MOSFET and forward biases the NPN transistor's base as the current increases. As the NPN turns on, it begins to pull gate drive current through R1, dropping the gate drive voltage across it, and thus lowering the voltage across the gate-to-source of the power MOSFET and limiting the current. The current limit is temperature dependent as shown in Figure 3, and decreases from about 2.3 Amps at 25°C to about 1.3 Amps at 150°C.

Since the MLP1N06CL continues to conduct current and dissipate power during a shorted load condition, it is important to provide sufficient heatsinking to limit the device junction temperature to a maximum of 150°C.

The metal current sense resistor R2 adds about 0.4 ohms to the power MOSFET's on-resistance, but the effect of temperature on the combination is less than on a standard MOSFET due to the lower temperature coefficient of R2. The on-resistance variation with temperature for gate voltages of 4 and 5 Volts is shown in Figure 5.

Back-to-back polysilicon diodes between gate and source provide ESD protection to greater than 2 kV, HBM. This on-chip protection feature eliminates the need for an external Zener diode for systems with potentially heavy line transients.

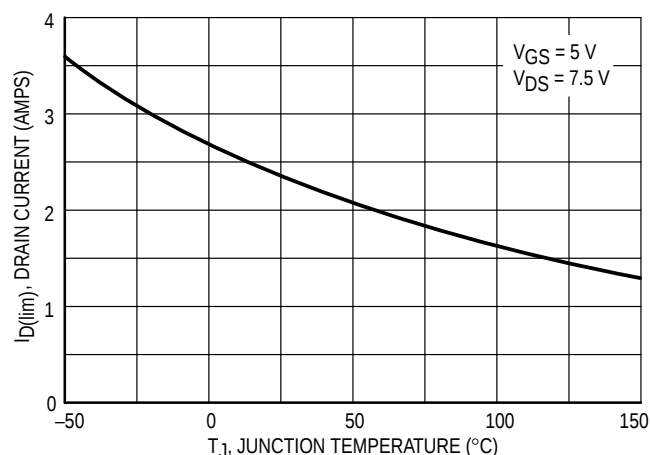


Figure 3. $I_{D(lim)}$ Variation With Temperature

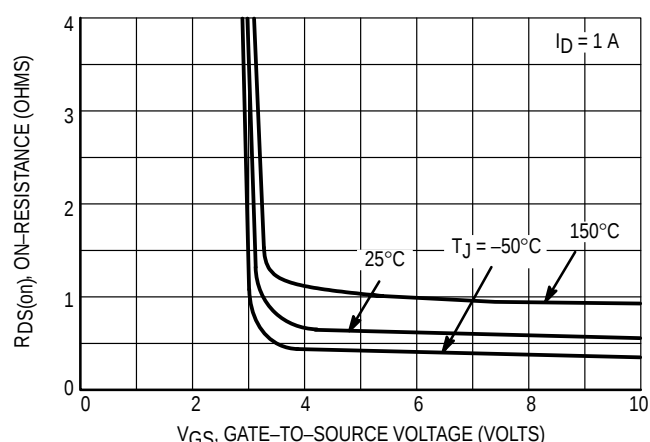


Figure 4. $R_{DS(on)}$ Variation With Gate-To-Source Voltage

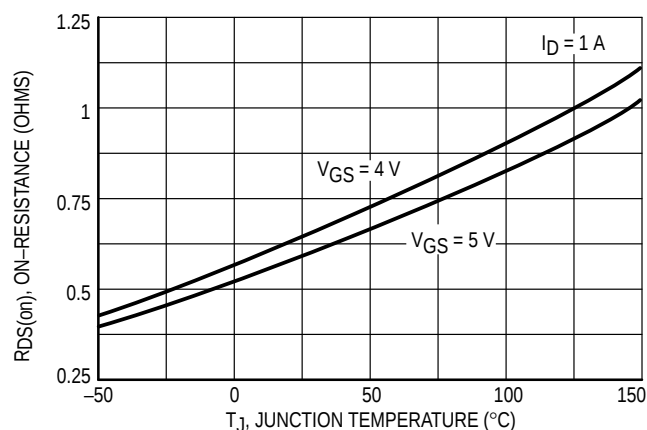


Figure 5. On-Resistance Variation With Temperature

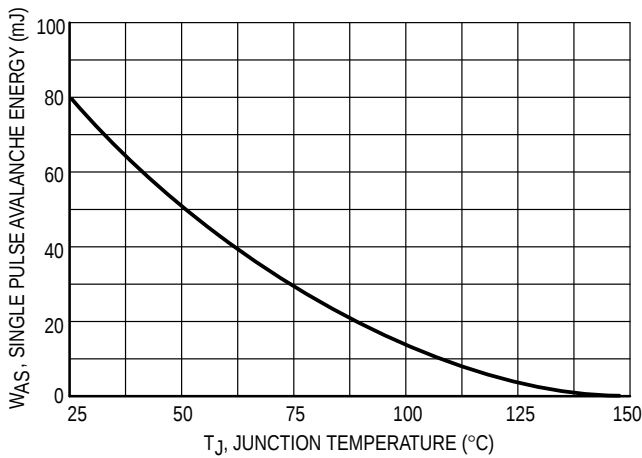


Figure 6. Single Pulse Avalanche Energy versus Junction Temperature

FORWARD BIASED SAFE OPERATING AREA

The FBSOA curves define the maximum drain-to-source voltage and drain current that a device can safely handle when it is forward biased, or when it is on, or being turned on. Because these curves include the limitations of simultaneous high voltage and high current, up to the rating of the device, they are especially useful to designers of linear systems. The curves are based on a case temperature of 25°C and a maximum junction temperature of 150°C. Limitations for repetitive pulses at various case temperatures can be determined by using the thermal response curves. Motorola Application Note, AN569, "Transient Thermal Resistance — General Data and Its Use" provides detailed instructions.

MAXIMUM DC VOLTAGE CONSIDERATIONS

The maximum drain-to-source voltage that can be continuously applied across the MLP1N06CL when it is in current limit is a function of the power that must be dissipated. This power is determined by the maximum current limit at maximum rated operating temperature (1.8 A at 150°C) and not the R_{DS(on)}. The maximum voltage can be calculated by the following equation:

$$V_{\text{supply}} = \frac{(150 - T_A)}{I_{D(\text{lim})} (R_{\theta\text{JC}} + R_{\theta\text{CA}})}$$

where the value of R_{θCA} is determined by the heatsink that is being used in the application.

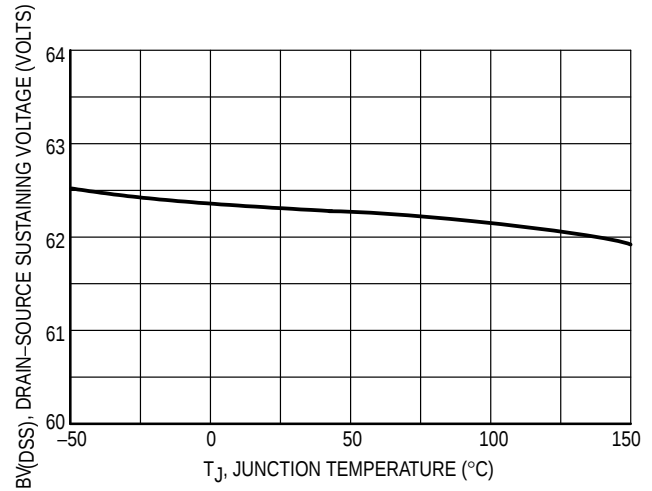


Figure 7. Drain-Source Sustaining Voltage Variation With Temperature

DUTY CYCLE OPERATION

When operating in the duty cycle mode, the maximum drain voltage can be increased. The maximum operating temperature is related to the duty cycle (DC) by the following equation:

$$T_C = (V_{DS} \times I_D \times DC \times R_{\theta\text{CA}}) + T_A$$

The maximum value of V_{DS} applied when operating in a duty cycle mode can be approximated by:

$$V_{DS} = \frac{150 - T_C}{I_{D(\text{lim})} \times DC \times R_{\theta\text{JC}}}$$

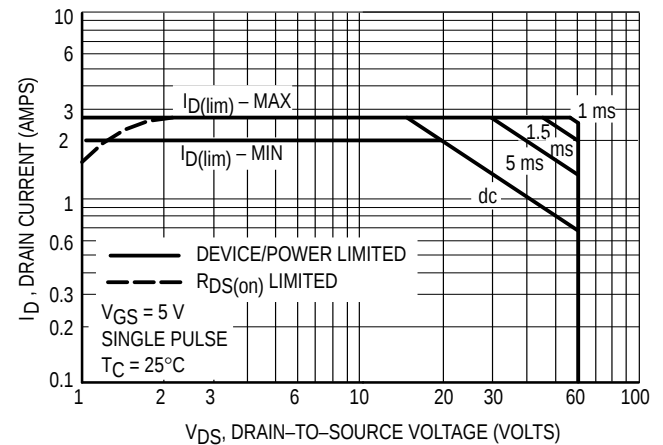


Figure 8. Maximum Rated Forward Bias Safe Operating Area (MLP1N06CL)

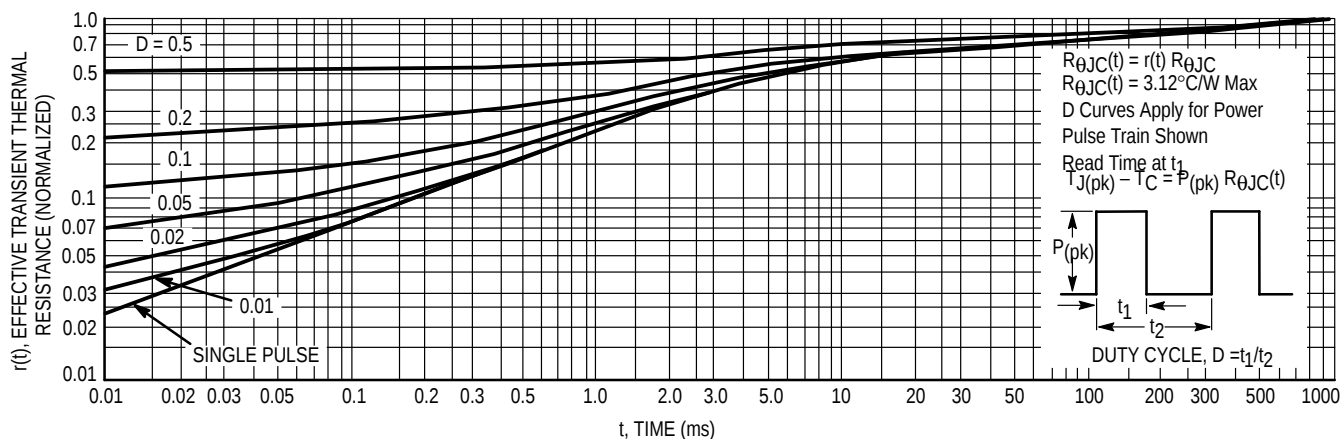


Figure 9. Thermal Response (MLP1N06CL)

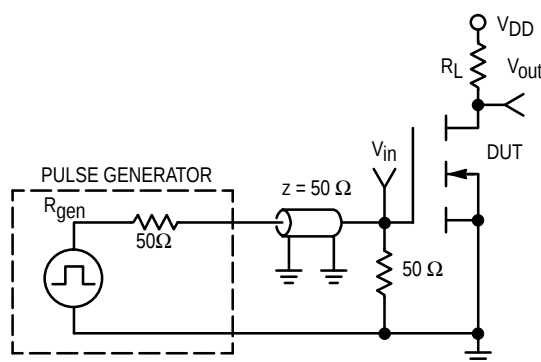


Figure 10. Switching Test Circuit

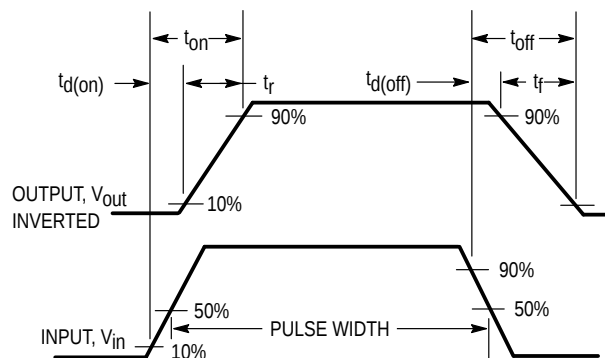


Figure 11. Switching Waveforms

ACTIVE CLAMPING

SMARTDISCRETES technology can provide on-chip realization of the popular gate-to-source and gate-to-drain Zener diode clamp elements. Until recently, such features have been implemented only with discrete components which consume board space and add system cost. The SMARTDISCRETES technology approach economically melds these features and the power chip with only a slight increase in chip area.

In practice, back-to-back diode elements are formed in a polysilicon region monolithically integrated with, but electrically isolated from, the main device structure. Each back-to-back diode element provides a temperature compensated voltage element of about 7.2 volts. As the polysilicon region is formed on top of silicon dioxide, the diode elements are free from direct interaction with the conduction regions of the power device, thus eliminating parasitic electrical effects while maintaining excellent thermal coupling.

To achieve high gate-to-drain clamp voltages, several voltage elements are strung together; the MLP1N06CL uses 8 such elements. Customarily, two voltage elements are used to provide a 14.4 volt gate-to-source voltage clamp. For the MLP1N06CL, the integrated gate-to-source voltage

elements provide greater than 2.0 kV electrostatic voltage protection.

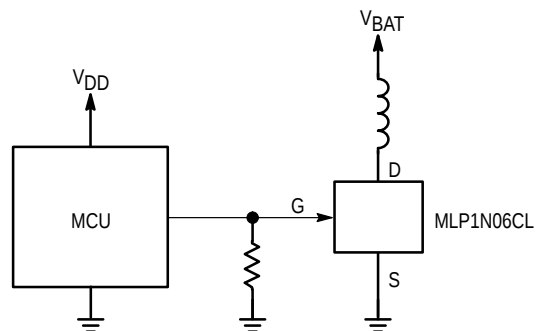
The avalanche voltage of the gate-to-drain voltage clamp is set less than that of the power MOSFET device. As soon as the drain-to-source voltage exceeds this avalanche voltage, the resulting gate-to-drain Zener current builds a gate voltage across the gate-to-source impedance, turning on the power device which then conducts the current. Since virtually all of the current is carried by the power device, the gate-to-drain voltage clamp element may be small in size. This technique of establishing a temperature compensated drain-to-source sustaining voltage (Figure 7) effectively removes the possibility of drain-to-source avalanche in the power device.

The gate-to-drain voltage clamp technique is particularly useful for snubbing loads where the inductive energy would otherwise avalanche the power device. An improvement in ruggedness of at least four times has been observed when inductive energy is dissipated in the gate-to-drain clamped conduction mode rather than in the more stressful gate-to-source avalanche mode.

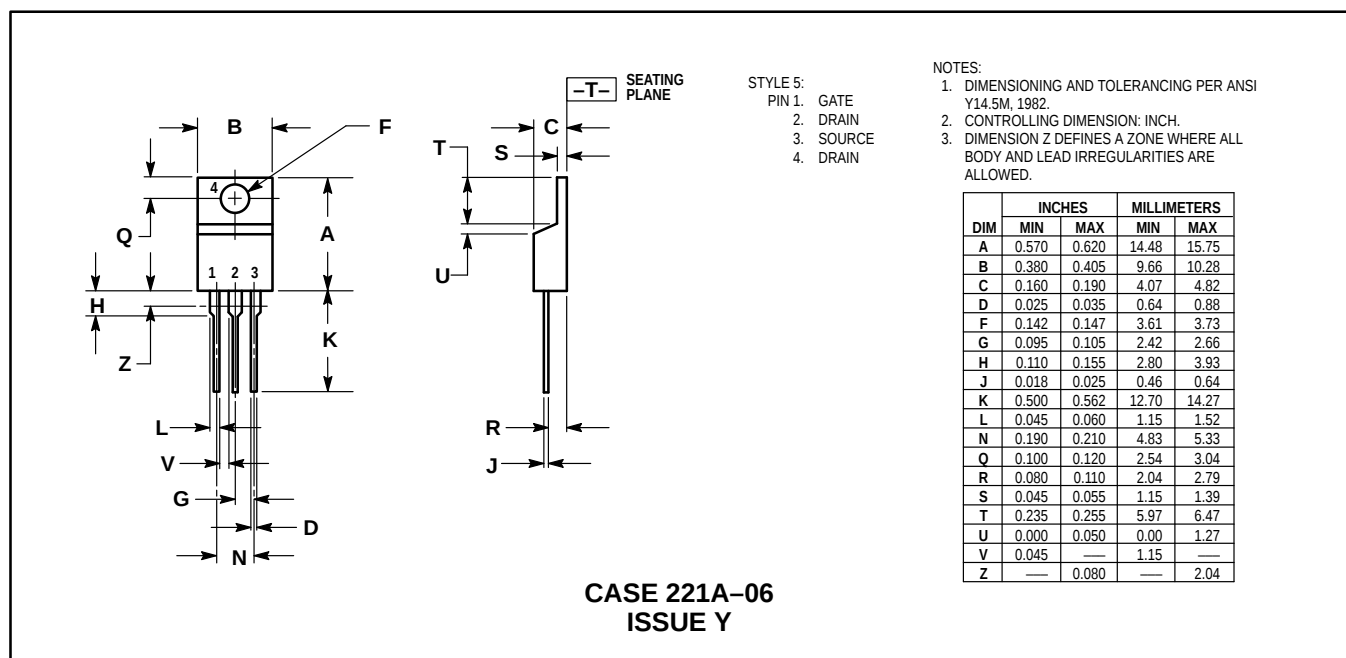
MLP1N06CL

TYPICAL APPLICATIONS: INJECTOR DRIVER, SOLENOIDS, LAMPS, RELAY COILS

The MLP1N06CL has been designed to allow direct interface to the output of a microcontrol unit to control an isolated load. No additional series gate resistance is required, but a 40 k Ω gate pulldown resistor is recommended to avoid a floating gate condition in the event of an MCU failure. The internal clamps allow the device to be used without any external transistor suppressing components.



PACKAGE DIMENSIONS



Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and  are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA / EUROPE: Motorola Literature Distribution;
P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609
INTERNET: <http://Design-NET.com>

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki,
6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298



MLP1N06CL/D

